

## **ABSTRACT**

Disclosed is a method of manufacturing a flash memory device. A sidewall oxidization process using a mixed gas of O<sub>2</sub> and TCA is implemented  
5 to reinforce isolation of the floating gate, and prevent a phenomenon that the thickness of the sidewall of the oxide film included within the dielectric film is thickened and a phenomenon that the thickness of the sidewall of the tunnel oxide film is thickened.